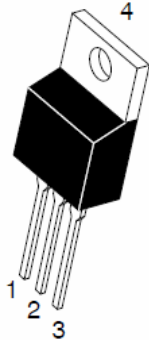
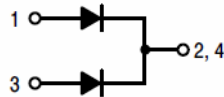
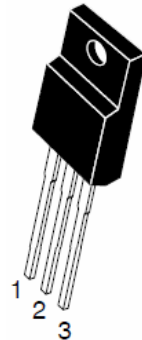


Trench MOS Barrier Schottky Rectifier

**TO-220AB
TSR16L45CT**



**ITO-220AB
TSR16L45CTF**



Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

Maximum ratings and electrical characteristics (T_J = 25°C unless otherwise noted)

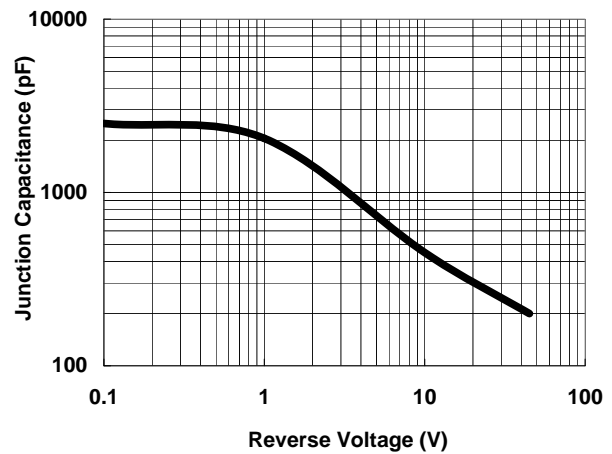
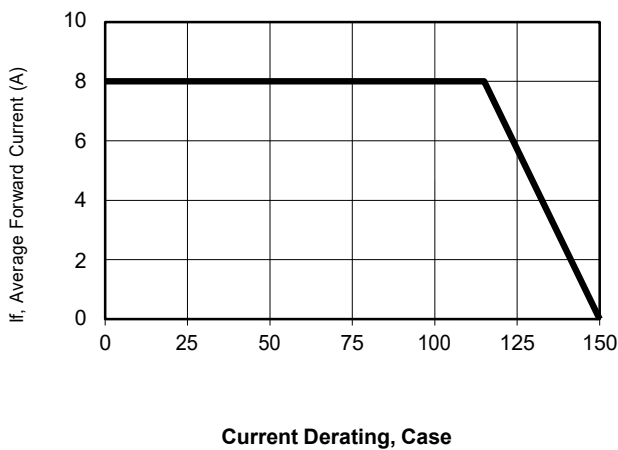
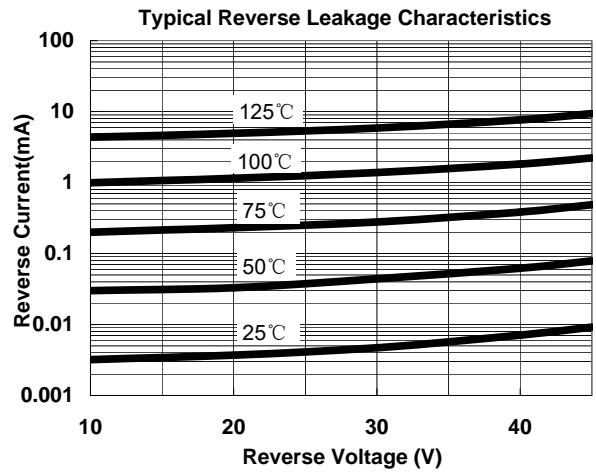
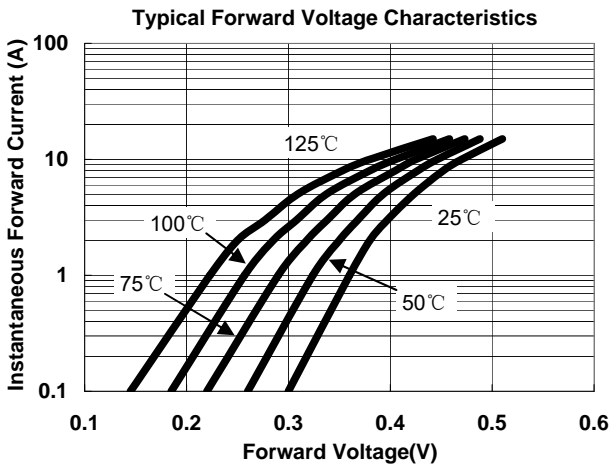
Parameter		Symbol	Limit		Unit
Maximum repetitive peak reverse voltage		VRRM	45		V
Maximum average forward rectified current	per device	IF(AV)	16		A
	per diode		8		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode		IFSM	220		A
Operating junction and storage temperature range		T _J , T _{STG}	-40 to +150		°C
Typical thermal resistance per leg	TO-220AB	R _{θJC}	2		°C/W
	ITO-220AB		4		°C/W
Instantaneous forward voltage per diode	I _F =4A	T _J =25°C	TYP.	MAX.	V
			0.45	-	
	I _F =8A	T _J =125°C	0.52	0.55	
			0.38	-	
I _F =8A	T _J =125°C	0.44	-		
		-	-		
Instantaneous reverse current per diode at rated reverse voltage	T _J =25°C	I _R (2)	50	100	uA
	T _J =125°C		-	50	mA

Notes:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

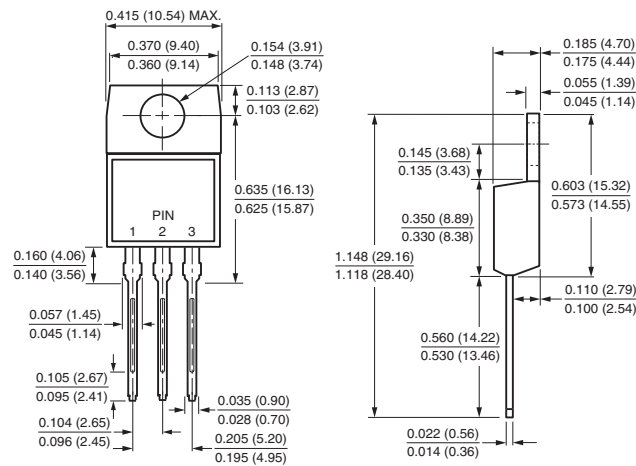
(2) Pulse test: Pulse width ≤ 40 ms

RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



PACKAGE OUTLINE DIMENSIONS

TO-220AB



ITO-220AB

